

RF1132 BROADBAND HIGH POWER SP3T SWITCH

Package Style: QFN, 12-pin, 2mmx2mm



Features

- Broadband Performance Low Frequency - 2.5 GHz
- Low Insertion Loss 0.48dB Typ at 0.90GHz 0.68dB Typ at 1.90GHz
- Good Isolation: 23dB Typ at 1.90GHz
- Excellent Cross-Modulation Performance: -102dBm Typ @ 0.90GHz -100dBm Typ @ 1.90GHz
- P0.1dB>34dBm
- Compact Footprint (2.0mmx2.0mmx0.55mm. 12-pin OFN)

Applications

- CDMA Handset Applications
- Antenna Tuning Applications
- IEEE802.11b/g WLAN Applications
- Multi-mode GSM/W-CDMA Applications
- GSM/GPRS/EDGE Switch Applications



Functional Block Diagram

Product Description

The RF1132 is a single-pole triple-throw (SP3T) switch designed for CDMA Handset Applications and general purpose switching applications which require very low insertion loss and high power handling capability. The RF1132 is ideally suited for battery operated applications requiring high performance switching with very low DC power consumption. The RF1132 features low insertion loss, excellent cross-modulation performance, and good isolation. It is fabricated with 0.5 µm GaAs pHEMT process, and is packaged in a very compact 2mmx2mm, 12-pin, leadless QFN package.

Ordering Information

RF1132 Broadband High Power SP3T Switch RF1132PCBA-410 Fully Assembled Evaluation Board

Optimum Technology Matching® Applied

GaAs HBT SiGe BiCMOS GaAs MESFET Si BiCMOS InGaP HBT SiGe HBT

GaAs pHEMT Gan Hemt Si CMOS Si BJT

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Absolute Maximum Ratings

Parameter	Rating	Unit
Voltage	6.0	V
Maximum Input Power (0.6GHz to 2.5GHz), RF1, RF2, RF3	+36	dBm
Operating Temperature	-30 to +85	°C
Storage Temperature	-65 to +100	°C



Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

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Devenator	Specification		11	Opendition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
					$V_{CONTROL}$ =0/2.6V, Nominal Test Conditions Unless Otherwise Specified: Z0=50 Ω . Temp=25°C. Need external DC blocking capacitors on all RF ports.	
Operating Frequency	0.6		2.5	GHz		
Insertion Loss						
Cellular		0.48	0.58	dB	ANT to RFx ON, 824 MHz to 894 MHz	
GPS		0.60	0.70	dB	ANT to RFx ON, 1574 MHz to 1577 MHz	
PCS		0.68	0.78	dB	ANT to RFx ON, 1850MHz to 1990MHz	
RF>ANT Isolation						
Cellular	28	30		dB	RFxOFF to RFx ON, 824 MHz to 894 MHz	
GPS	23	25		dB	RFxOFF to RFx ON, 1574 MHz to 1577 MHz	
PCS	21	23		dB	RFxOFF to RFx ON, 1850MHz to 1990MHz	
Second Harmonics						
Cellular		-82	-78	dBc	+26dBm input	
PCS		-84	-80	dBc	+26dBm input	
Third Harmonics						
Cellular		-91	-80	dBc	+26dBm input	
PCS		-95	-82.5	dBc	+26dBm input	
IIP3						
IIP3 - Cellular (IMT, PCS, AWS)	64	65		dBm	Two tones: +23dBm, 837MHz and 838MHz	
		67		dBm	Two tones: +23 dBm, 837 MHz and 838 MHz, $V_{CONTROL}$ =3V	
IIP3 - PCS	61	63		dBm	Two tones: +23dBm, 1880MHz and 1881MHz	
		65		dBm	Two tones: +23dBm, 1880MHz and 1881MHz, V _{CONTROL} =3V	
Cross-Modulation						
Cellular		-102	-101	dBm	PTx1=23dBm @ 836MHz, PTx2=23dBm @ 837MHz; P _{INT} =-23dBm @ 881.5MHz	
		-105		dBm	PTx1=23dBm @ 836MHz, PTx2=23dBm @ 837MHz; P _{INT} =-23dBm @ 881.5MHz, V _{CONTROL} =3V	
PCS		-100	-96	dBm	PTx1=23dBm @ 1879.5MHz, PTx2=23dBm @ 1880.5MHz; P _{INT} =-23dBm @ 1960MHz	
		-102		dBm	PTx1=23dBm @ 1879.5MHz, PTx2=23dBm @ 1880.5MHz; P _{INT} =-23dBm @ 1960MHz, V _{CONTROL} =3V	







Paramotor	Specification			Unit	Condition	
Farameter	Min.	Тур.	Max.	Unit	Condition	
RF Port Return Loss						
RF>ANT		-24	-15	dB	0.5GHz to 2.0GHz	
Input Power at 0.1dB Compression Point						
Cellular		>+35		dBm		
PCS		>+35		dBm		
Switching Speed						
T _{RISE} , T _{FALL}		0.80	1	us	10% to 90% RF, 90% to 10% RF	
T _{ON} , T _{OFF}		0.80	1	μs	50% control to 90% RF, 50% control to 90% RF	
DC Controls						
V _{High} (V1, V2, V3)		2.6	3.6	V		
V _{LOW} (V1, V2, V3)	0		0.4	V		
Control Current		10		μΑ		
Leakage Current		10		μA		

Switch Control Settings

V1	V2	V3	ANT-RF1	ANT-RF2	ANT-RF3
1	0	0	ON	OFF	OFF
0	1	0	OFF	ON	OFF
0	0	1	OFF	OFF	ON

0: Logic level low, 0V to 0.4V

1: Logic level high, 2.6V to 3.6V

Note: Indeterminate states would lead to degraded performance.



Pin	Function	Description
1	V3	Control Signal 3
2	RF3	RF Port 3
3	GND	Ground
4	GND	Ground
5	RF2	RF Port 2
6	V2	Control Signal 2
7	GND	Ground
8	RF1	RF Port 1
9	V1	Control Signal 1.
10	GND	Ground
11	ANT	Antenna Connection
12	GND	Ground
Pkg Base	N/C	Should be left floating for best performance. RF performance specifications in this DS are quoted with package base left floating.







Package Drawing





Evaluation Board Schematic



Note: Package Base needs to be left floating for best Isolation performance.





Typical Performance



